

**N-CHANNEL ENHANCEMENT MODE MOSFET PLUS NPN TRANSISTOR**
**Features**

- N-Channel MOSFET and NPN Transistor in One Package
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **ESD Protected MOSFET Gate up to 2kV**
- **Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

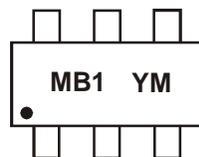
**Mechanical Data**

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)


**Ordering Information (Note 3)**

Part Number	Case	Packaging
DMB53D0UV-7	SOT563	3000/Tape & Reel
DMB53D0UV-13	SOT563	10000/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. No purposely added lead. Halogen and Antimony free
  2. Diodes Inc.'s "Green" policy can be found on our website at <http://www.diodes.com>.
  3. For packaging details, go to our website at <http://www.diodes.com>.

**Marking Information**


MB1 = Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: V = 2008)  
 M = Month (ex: 9 = September)

## Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	V	W	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings – MOSFET, Q1** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DSS}$	50	V
Gate-Source Voltage	$V_{GSS}$	$\pm 12$	V
Drain Current (Note 4)	$I_D$	160	mA
Pulsed Drain Current (Note 4)	$I_{DM}$	560	mA

**Maximum Ratings - NPN Transistor, Q2** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	50	V
Collector-Emitter Voltage	$V_{CEO}$	45	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current	$I_C$	100	mA

**Thermal Characteristics, Total Device** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 1)	$P_D$	250	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	500	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

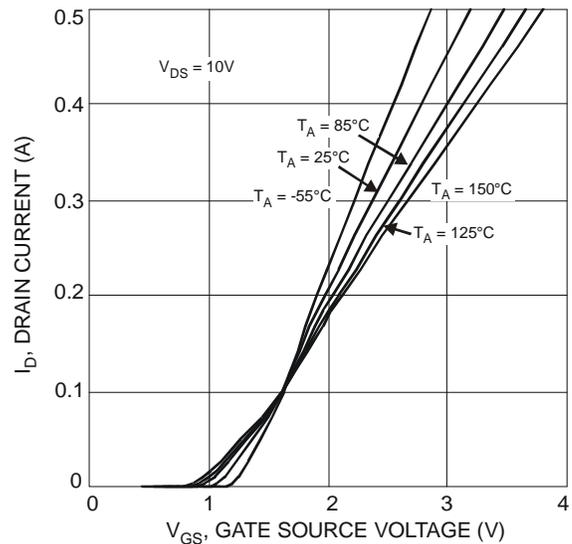
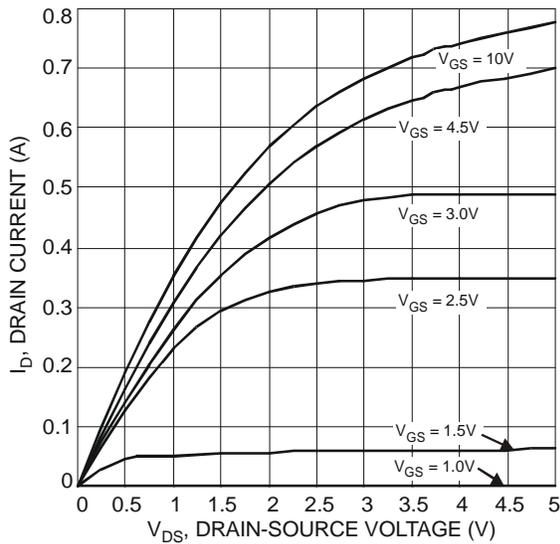
**Electrical Characteristics - MOSFET** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 5)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	50	—	—	V	$V_{GS} = 0V, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	10	$\mu\text{A}$	$V_{DS} = 50V, V_{GS} = 0V$
Gate-Body Leakage	$I_{GSS}$	—	—	1.0 5.0	$\mu\text{A}$	$V_{GS} = \pm 8V, V_{DS} = 0V$ $V_{GS} = \pm 12V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 5)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	0.7	0.8	1.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	3.1	4	$\Omega$	$V_{GS} = 4V, I_D = 100\text{mA}$
		—	4	5		$V_{GS} = 2.5V, I_D = 80\text{mA}$
Forward Transconductance	$g_{FS}$	180	—	—	mS	$V_{DS} = 10V, I_D = 100\text{mA}, f = 1.0\text{KHz}$
<b>DYNAMIC CHARACTERISTICS (Note 6)</b>						
Input Capacitance	$C_{iss}$	—	25	—	pF	$V_{DS} = 10V, V_{GS} = 0V, f = 1.0\text{MHz}$
Output Capacitance	$C_{oss}$	—	5	—	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	2.1	—	pF	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

**Electrical Characteristics - NPN Transistor** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage (Note 5)	$V_{(BR)CBO}$	50	—	—	V	$I_C = 10\mu\text{A}, I_B = 0$
Collector-Emitter Breakdown Voltage (Note 5)	$V_{(BR)CEO}$	45	—	—	V	$I_C = 10\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage (Note 5)	$V_{(BR)EBO}$	6	—	—	V	$I_E = 1\mu\text{A}, I_C = 0$
DC Current Gain (Note 5)	$h_{FE}$	200	290	450	—	$V_{CE} = 5.0\text{V}, I_C = 2.0\text{mA}$
Collector-Emitter Saturation Voltage (Note 5)	$V_{CE(SAT)}$	—	—	100 300	mV	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$ $I_C = 100\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Saturation Voltage (Note 5)	$V_{BE(SAT)}$	—	700 900	—	mV	$I_C = 10\text{mA}, I_B = 0.5\text{mA}$ $I_C = 100\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Voltage (Note 5)	$V_{BE}$	580 —	660 —	700 770	mV	$V_{CE} = 5.0\text{V}, I_C = 2.0\text{mA}$ $V_{CE} = 5.0\text{V}, I_C = 10\text{mA}$
Collector-Cutoff Current (Note 5)	$I_{CBO}$	—	—	15	nA	$V_{CB} = 30\text{V}$
Collector-Emitter Cut-Off Current (Note 5)	$I_{CES}$	—	—	5.0	$\mu\text{A}$	$V_{CB} = 30\text{V}, T_A = 150^\circ\text{C}$
Gain Bandwidth Product	$f_T$	—	—	100	nA	$V_{CE} = 45\text{V}$
Gain Bandwidth Product	$f_T$	100	—	—	MHz	$V_{CE} = 5.0\text{V}, I_C = 10\text{mA}, f = 100\text{MHz}$
Output Capacitance	$C_{OBO}$	—	—	4.5	pF	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}$
Noise Figure	NF	—	—	10	dB	$V_{CE} = 5\text{V}, R_S = 2.0\text{k}\Omega, f = 1.0\text{kHz}, BW = 200\text{Hz}$

**MOSFET**


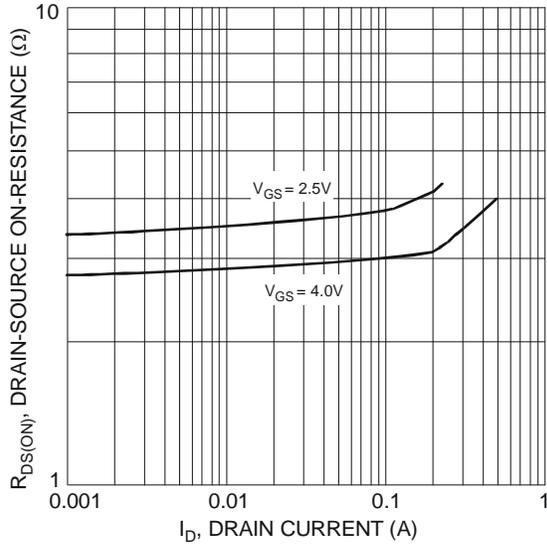


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

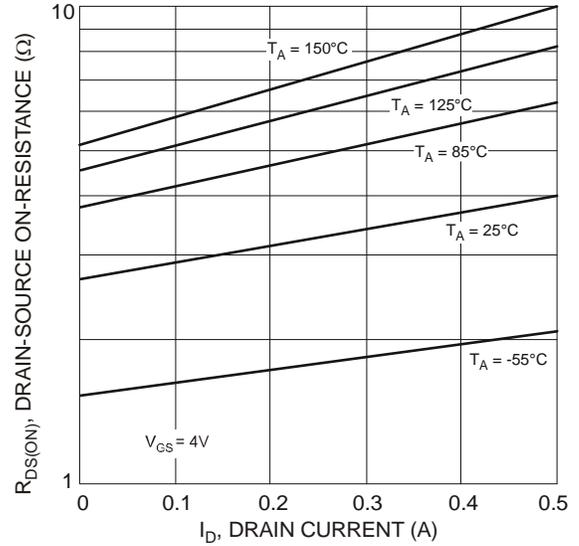


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

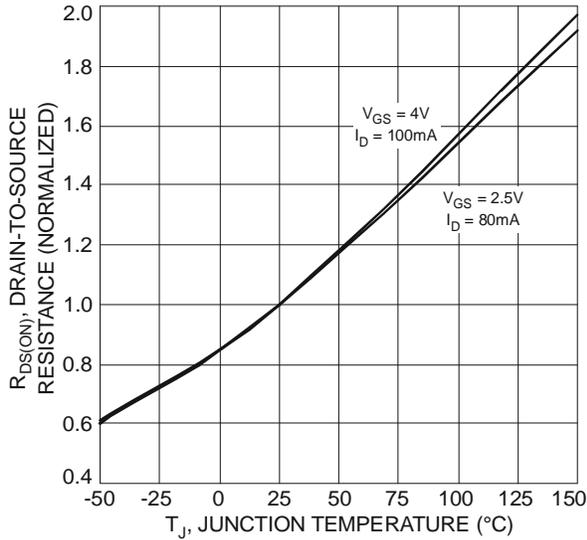


Fig. 5 On-Resistance Variation with Temperature

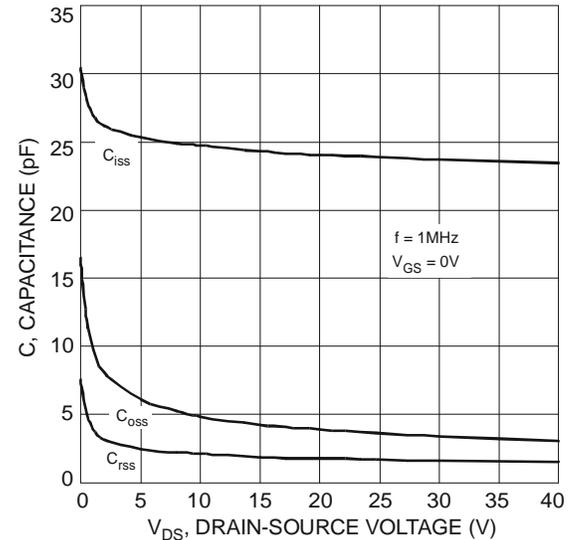


Fig. 6 Typical Capacitance

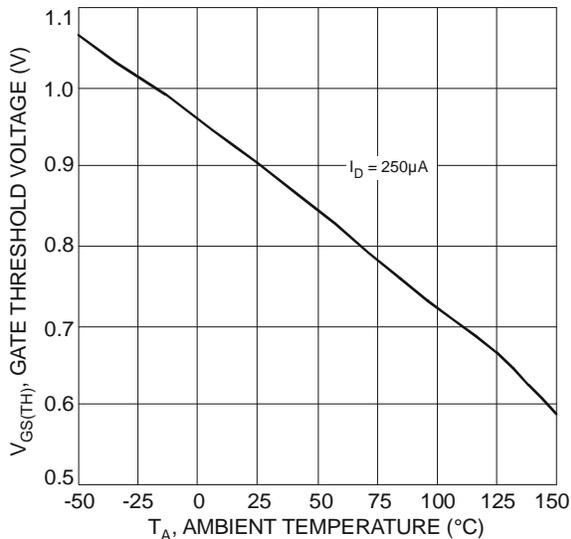


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

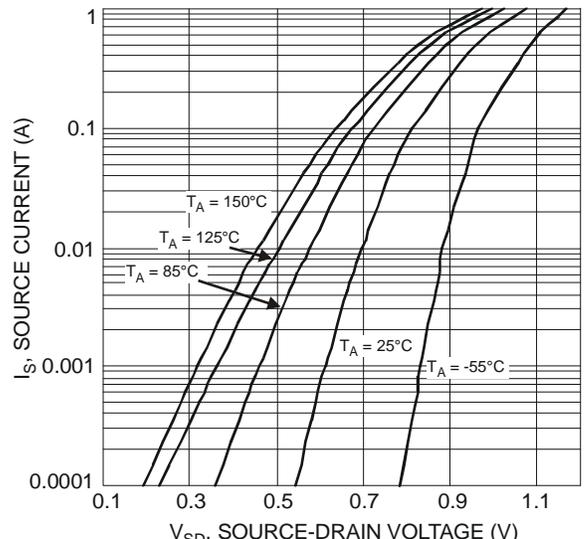
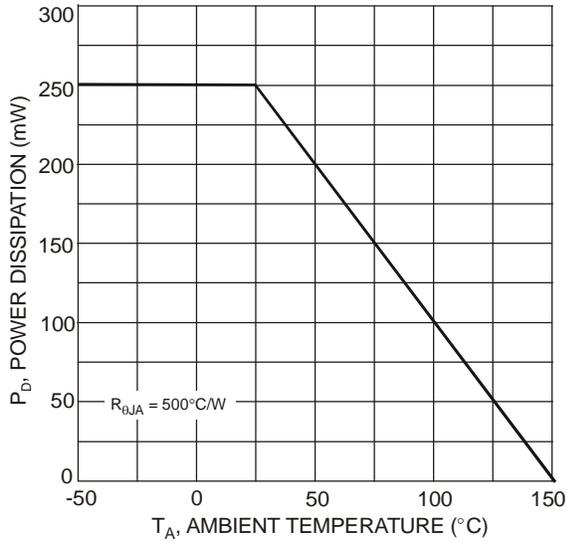
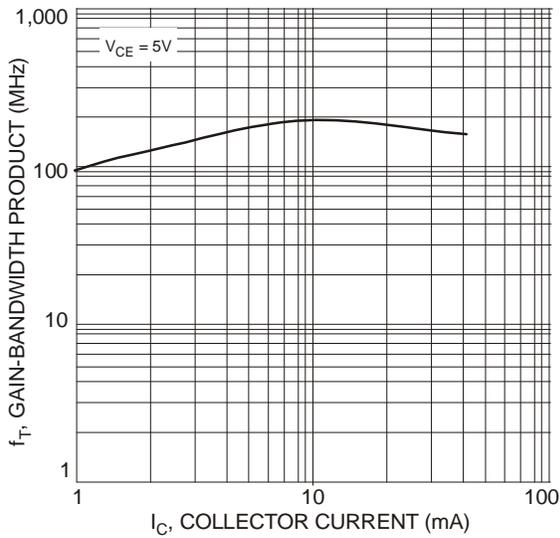
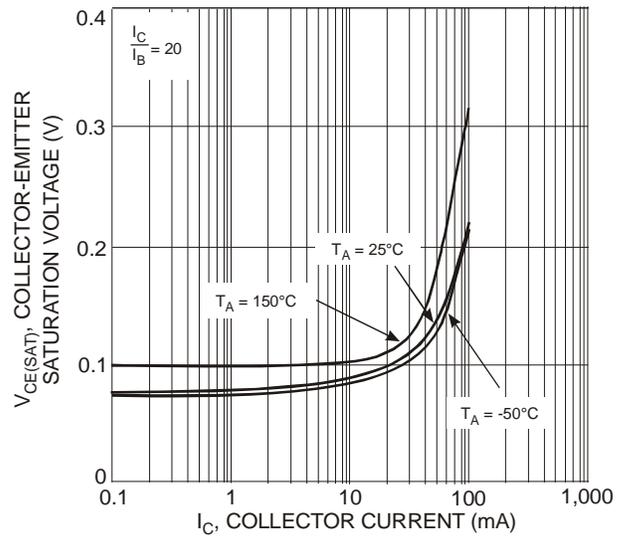
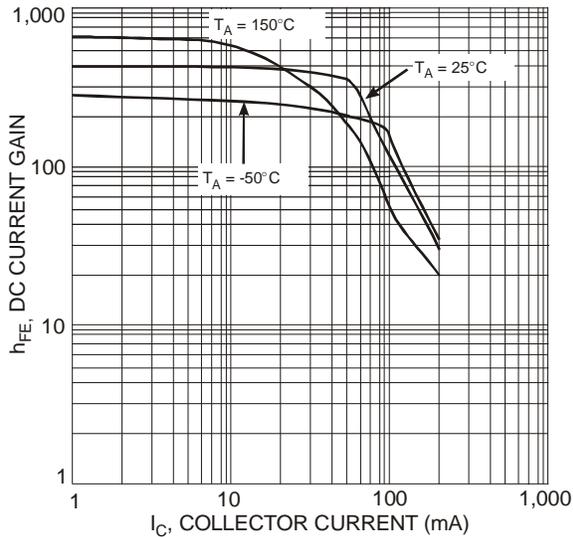


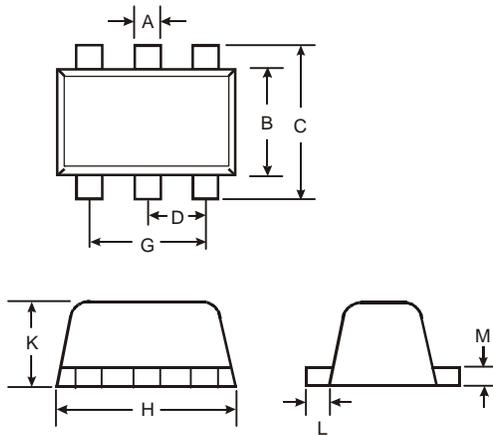
Fig. 8 Diode Forward Voltage vs. Current



**NPN Transistor**

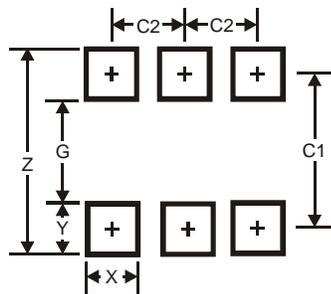


**Package Outline Dimensions**



SOT563			
Dim	Min	Max	Typ
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	-	-	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5

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